Central™
Semiconductor Corp.

PROCESS CPS090

Silicon Controlled Rectifier

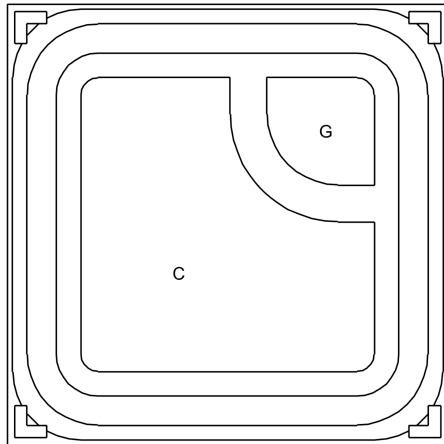
8.0 Amp Sensitive Gate SCR Chip

www.DataSheet4U.com

PROCESS DETAILS

Process	Glass Passivated Mesa
Die Size	90 x 90 MILS
Die Thickness	8.7 MILS
Cathode Bonding Pad Area	60 x 30 MILS
Gate Bonding Pad Area	22 x 22 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Al/Mo/Ni/Ag - 32,000Å

GEOMETRY



GROSS DIER PER 4 INCH WAFER
1,310

PRINCIPAL DEVICE TYPES
CS220-8M Series
CSD-8M Series
CSDD-8M Series

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

R0 (4- January 2006)

www.DataSheet4U.com